

N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK Rev. 4 — 27 September 2011 Product data sh

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection

Load switching

Improved mechanical and thermal characteristics

- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	51	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	29.3	mΩ
		V _{GS} = 10 V; I _D = 15 A;	-	12.7	16.3	mΩ

 $T_i = 25 \text{ °C}; \text{ see Figure 13}$



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Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 30 A;	-	16	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	54	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	87	mJ

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. C	Ordering	ng information			
Type number		Package			
		Name	Description	Version	
PSMN016-1	00YS	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669	

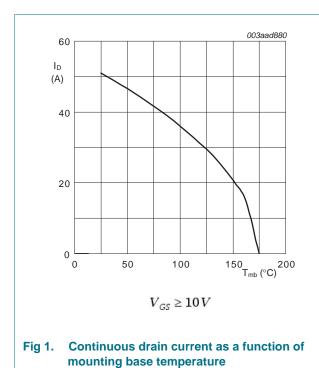
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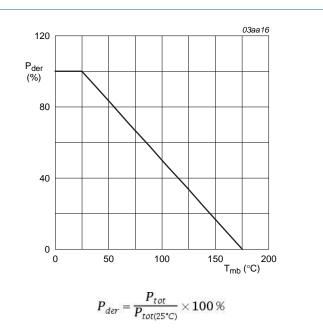
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	T _j ≤ 175 °C; T _j ≥ 25 °C; R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	36	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	51	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	204	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	117	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dra	ain diode				
ls	source current	T _{mb} = 25 °C	-	51	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	204	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 51 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	87	mJ

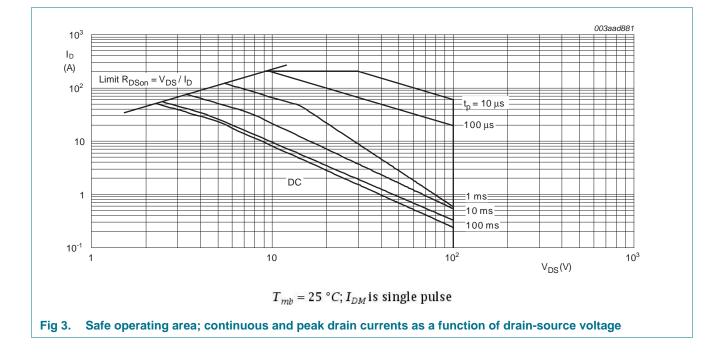






PSMN016-100YS

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ТП

5. Thermal characteristics

TH

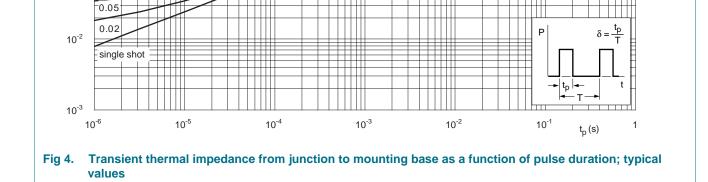
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.54	1.28	K/W
1				0	03aad882	
Z _{th(j-mb)} (K/W)	$\delta = 0.5$					

Table 5. Thermal characteristics

0.2

0.1

10⁻¹



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
	voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
V _{GS(th)} gate-source th	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.7	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	100	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.04	2	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	29.3	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	28.7	45.6	mΩ
	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	12.7	16.3	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.6	1.5	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	42	-	nC
		$I_D = 30 \text{ A}; \text{ V}_{DS} = 50 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$	-	54	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	11	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I_D = 30 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 14</u>	-	8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3.2	-	nC
Q _{GD}	gate-drain charge	$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	16	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.2	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	2744	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	205	-	pF
C _{rss}	reverse transfer capacitance		-	135	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	19	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ T_{j} = 25 \ ^{\circ}C$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	47	-	ns
t _f	fall time		-	21	-	ns

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003aad885

40 _{ID} (A) 50

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Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = 100 \text{ A}/\mu\text{s};$	-	56	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 50 V$	-	131	-	nC

100 g_{fs}

75

50

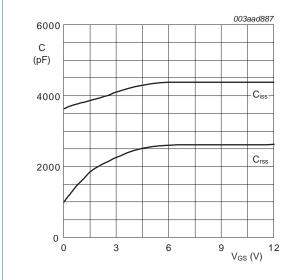
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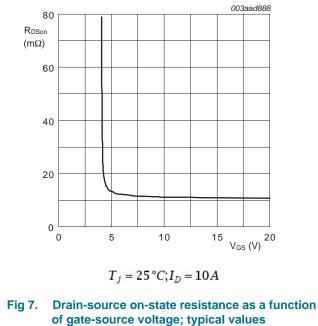
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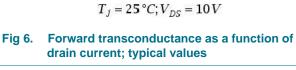
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 $V_{DS} = 0V; f = 1MHz$

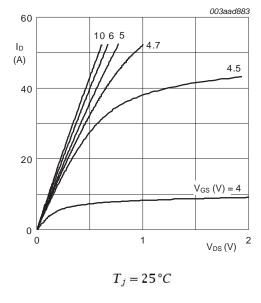






20

30



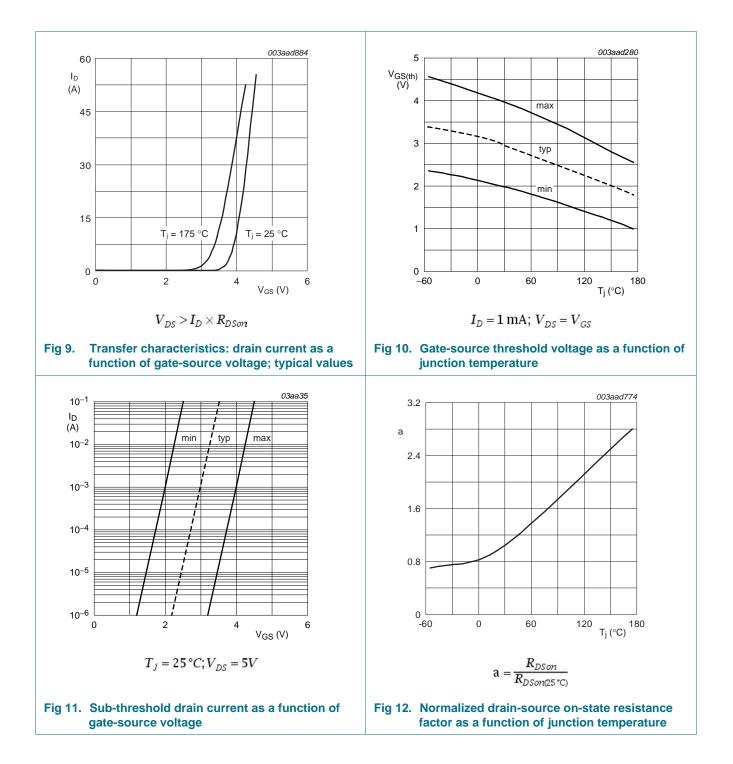
e as a function Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



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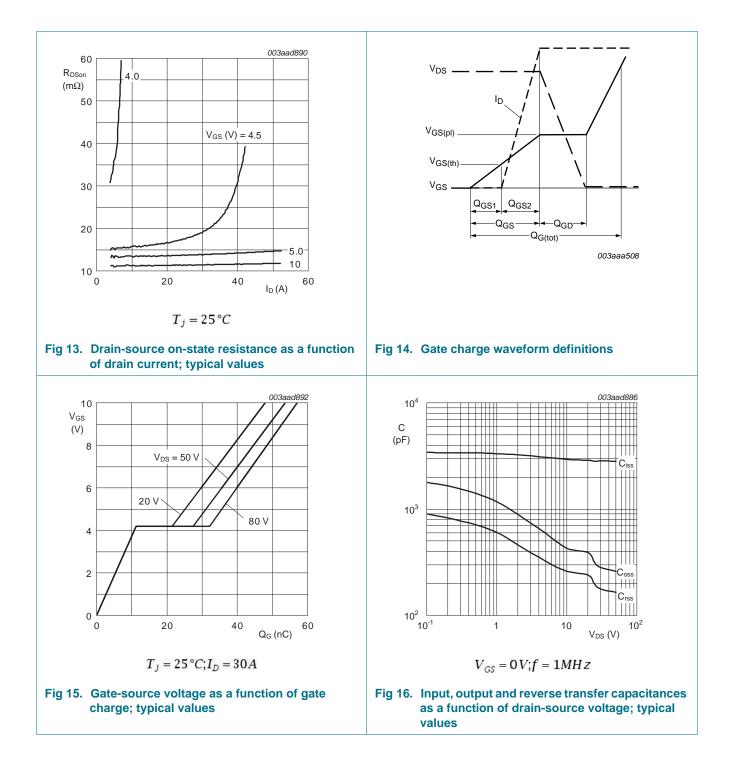
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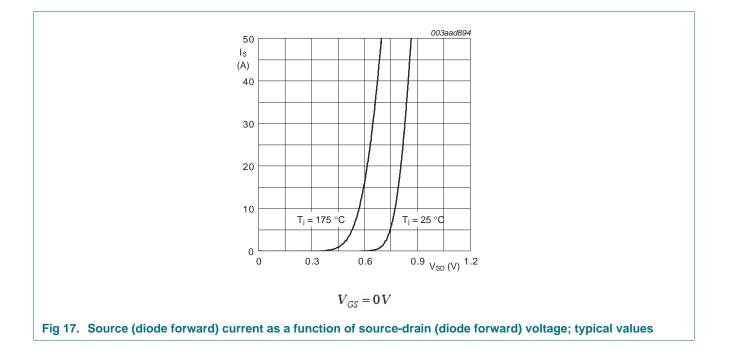
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7. Package outline

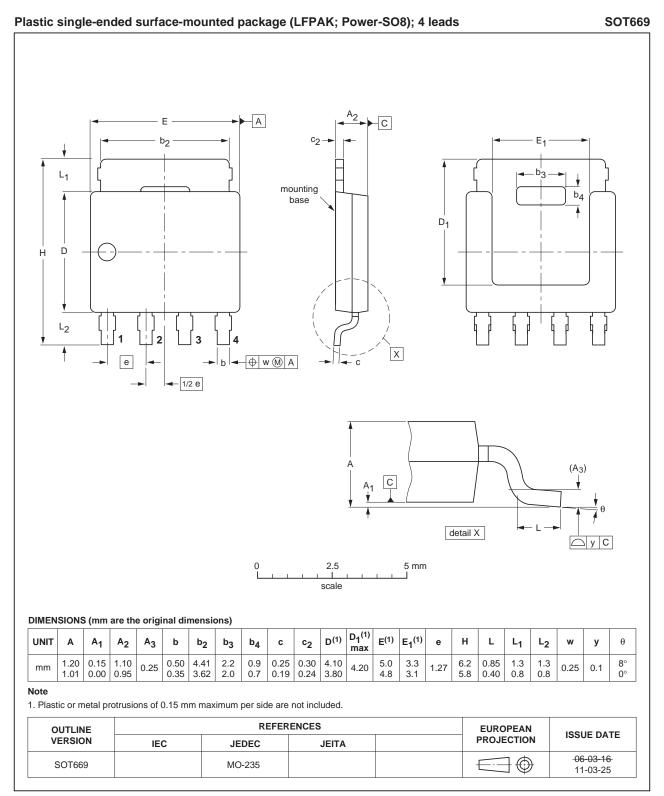


Fig 18. Package outline SOT669 (LFPAK; Power-SO8)

PSMN016-100YS Product data sheet

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8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100YS v.4	20110927	Product data sheet	-	PSMN016-100YS v.3
Modifications:	 Various changes t 	o content.		
PSMN016-100YS v.3	20100330	Product data sheet	-	PSMN016-100YS v.2

9. Legal information

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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